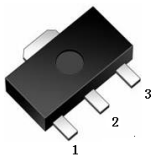
FEATURES

- Low $V_{CE(sat)}$: -0.2V(Typ) I_C/I_B=-500mA/-50mA
- Compliments 2SD1664

2SB1132 (PNP)



1. BASE
2. COLLECTO
3. EMITTER

SOT-89

Maximum Ratings (Ta=25 ℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	1	A
Collector Power dissipation	P_C	500	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55to +150	℃

ELECTRICAL CHARACTERISTICS (@ Ta=25 ℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=-50μA,I_E=0	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C=-1mA,I_B=0	-32			V
Emitter-base breakdown voltage	V_{EBO}	I_E=-50μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V,I_E=0			-0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.5	μA
DC current gain	h_{FE}	V_{CE}=-3V,I_C=-100mA	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA		-0.2	-0.5	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-50mA,f=30MHz		150		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		20	30	pF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	80-180	120-270	180-390
Marking	BAP	BAQ	BAR

2SB1132 Typical Characteristics

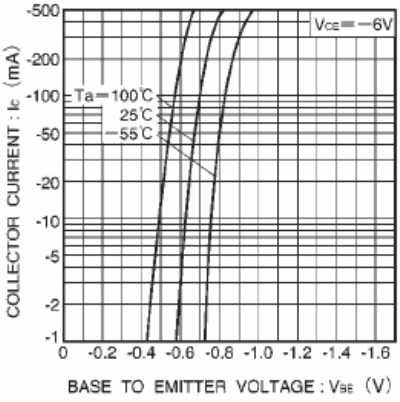


Fig.1 Grounded emitter propagation characteristics

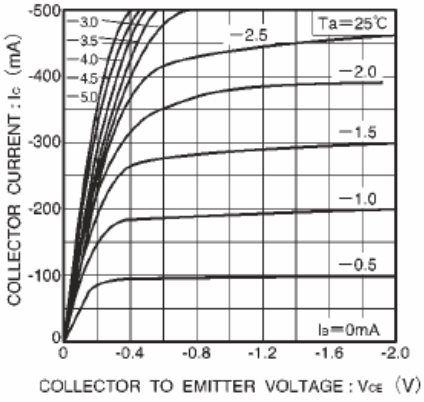


Fig.2 Grounded emitter output characteristics

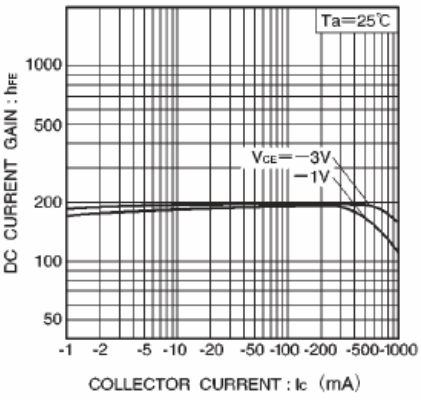


Fig.3 DC current gain vs. collector current (Ⅰ)

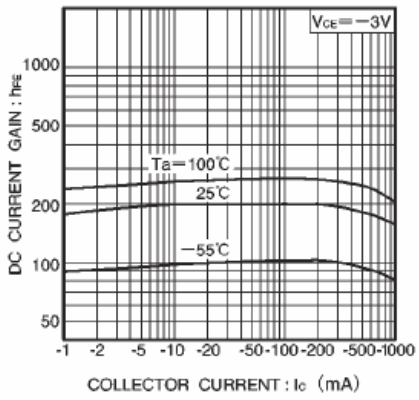


Fig.4 DC current gain vs. collector current (Ⅱ)

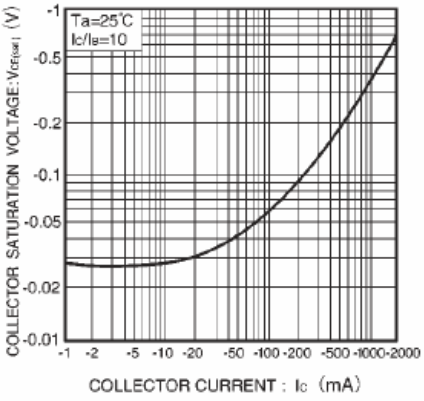


Fig.5 Collector-emitter saturation voltage vs. collector current

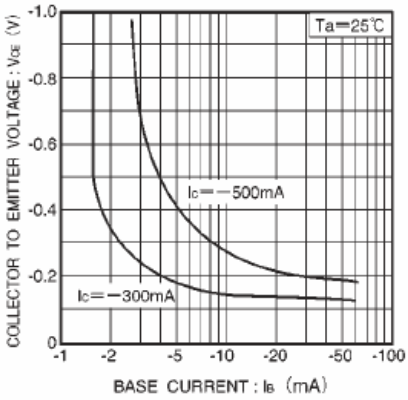


Fig.6 Collector-emitter saturation voltage vs. base current

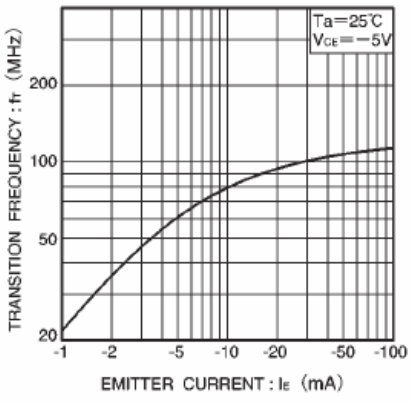


Fig.7 Gain bandwidth product vs. emitter current

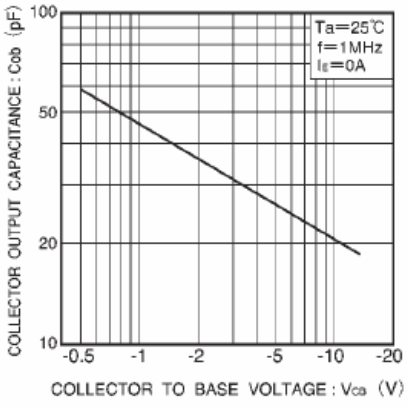


Fig.8 Collector output capacitance vs. collector-base voltage

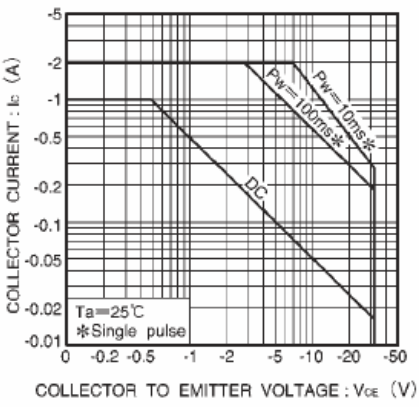


Fig.9 Safe operation area